

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
30V	14mΩ @ $V_{GS} = 10\text{V}$	10A
	20mΩ @ $V_{GS} = 4.5\text{V}$	8A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

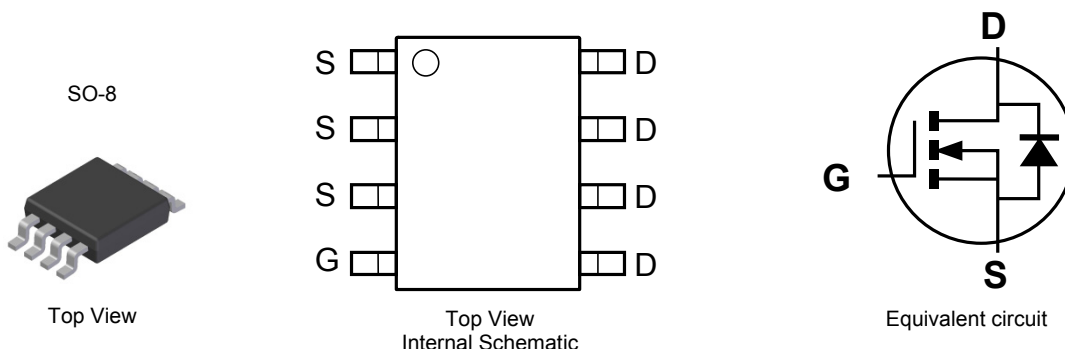
Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (approximate)

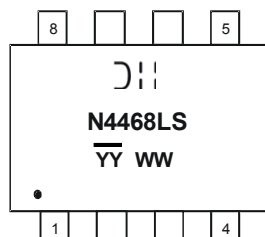


Ordering Information (Note 4)

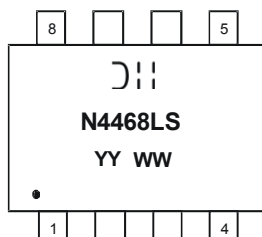
Part Number	Case	Packaging
DMN4468LSS-13	SO-8	2500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

DII = Manufacturer's Marking
 N4468LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	10	A
		T _A = +70°C		9	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	50	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.52	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	82	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	8.2	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	1.05	—	1.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	11	14	mΩ	V _{GS} = 10V, I _D = 11.6A
			15	20		V _{GS} = 4.5V, I _D = 10A
Forward Transfer Admittance	Y _{fs}	—	8	—	S	V _{DS} = 5V, I _D = 11.6A
Diode Forward Voltage	V _{SD}	—	0.73	0.95	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	867	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	85	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	81	—	pF	
Gate Resistance	R _g	—	1.39	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	18.85	—	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 11.6A
Gate-Source Charge	Q _{gs}	—	2.59	—	nC	
Gate-Drain Charge	Q _{gd}	—	6.15	—	nC	
Turn-On Delay Time	t _{D(on)}	—	5.46	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.3Ω, R _G = 3Ω, I _D = 1A
Turn-On Rise Time	t _r	—	14.53	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	18.84	—	ns	
Turn-Off Fall Time	t _f	—	6.01	—	ns	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

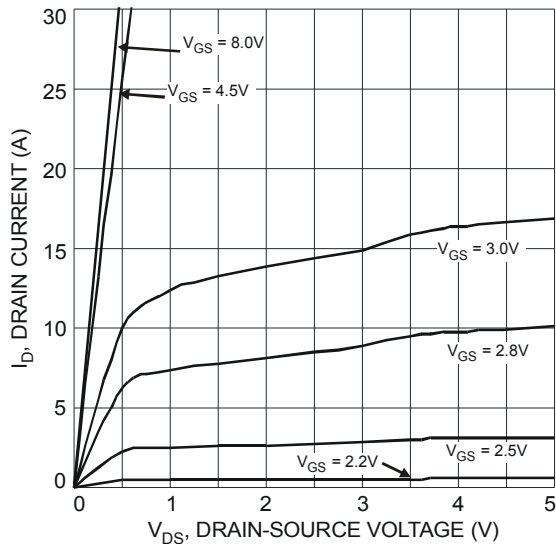


Fig. 1 Typical Output Characteristic

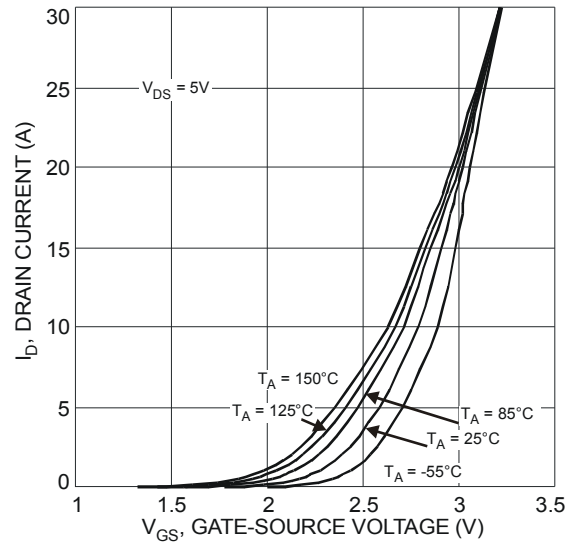


Fig. 2 Typical Transfer Characteristic

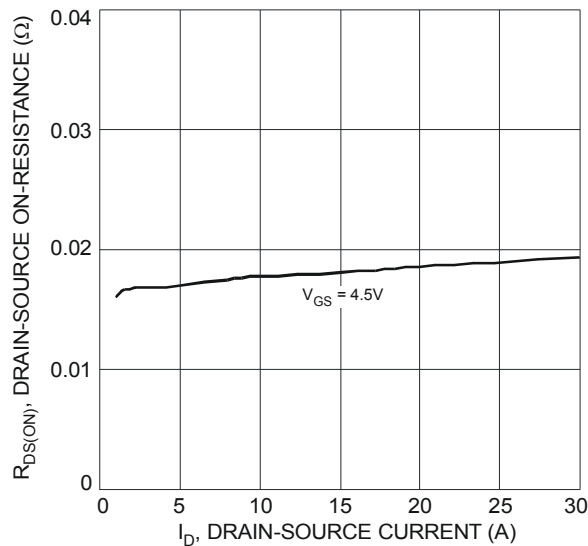


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

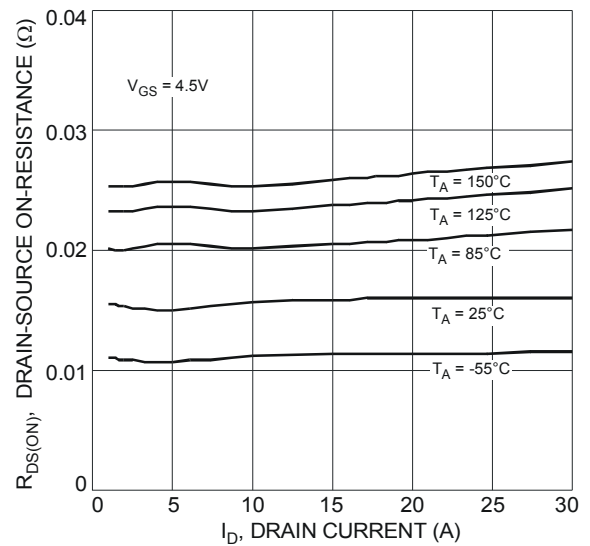


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

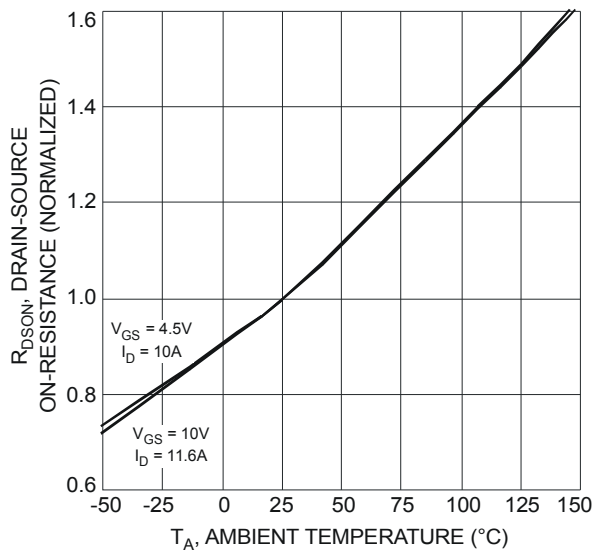


Fig. 5 On-Resistance Variation with Temperature

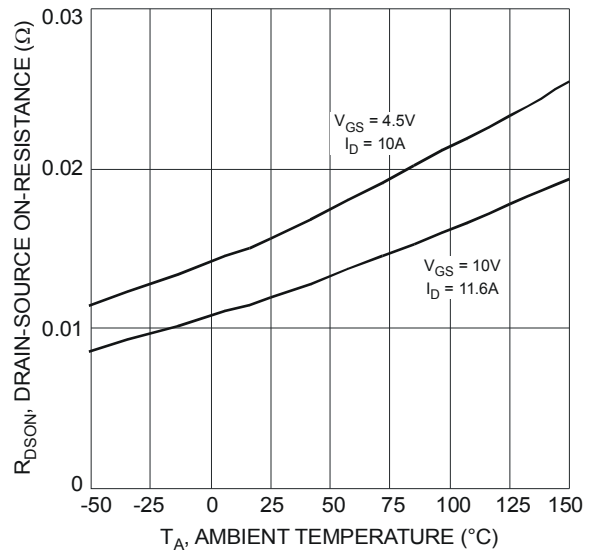


Fig. 6 On-Resistance Variation with Temperature

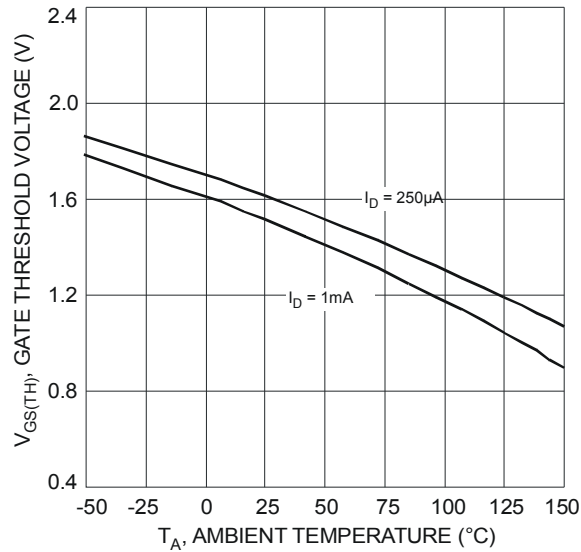


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

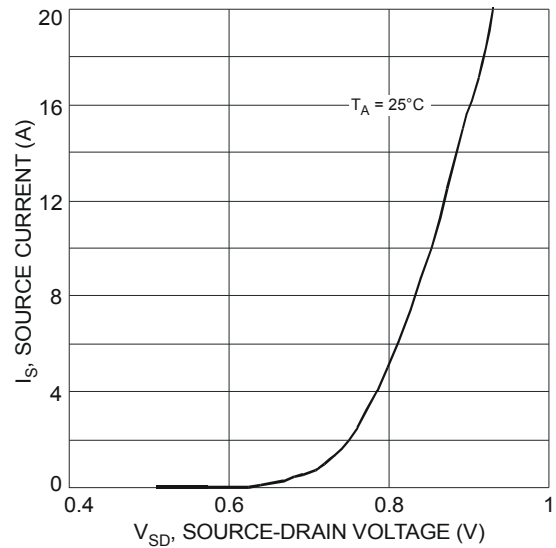


Fig. 8 Diode Forward Voltage vs. Current

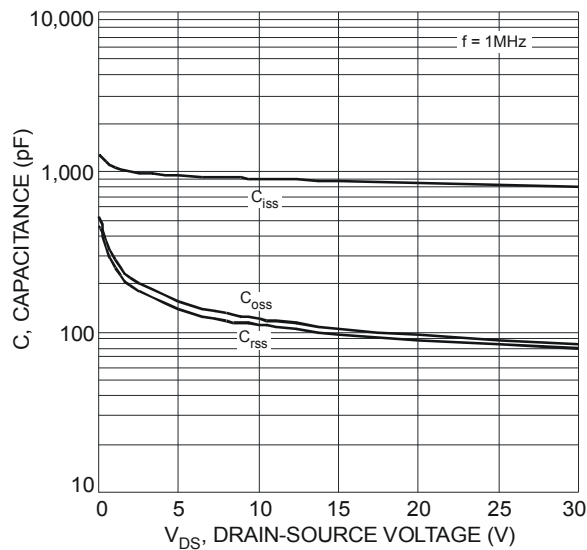


Fig. 9 Typical Total Capacitance

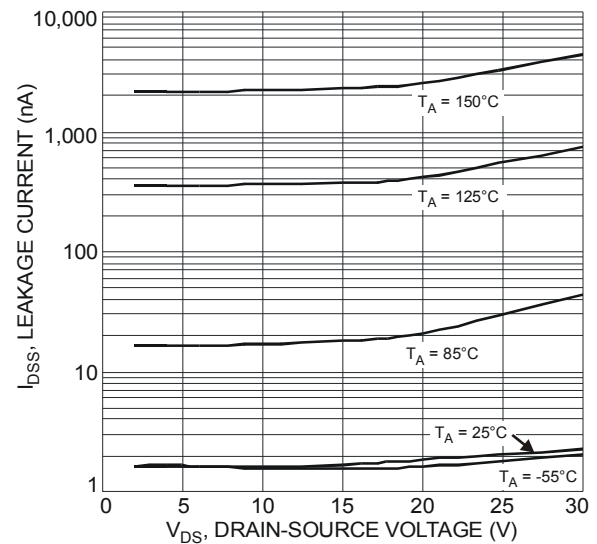


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

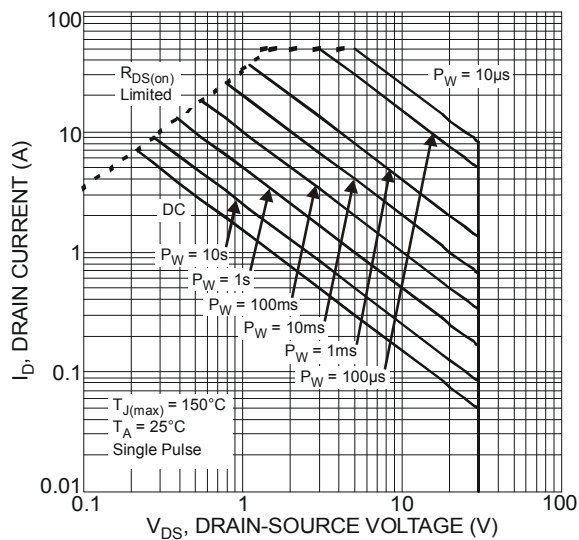
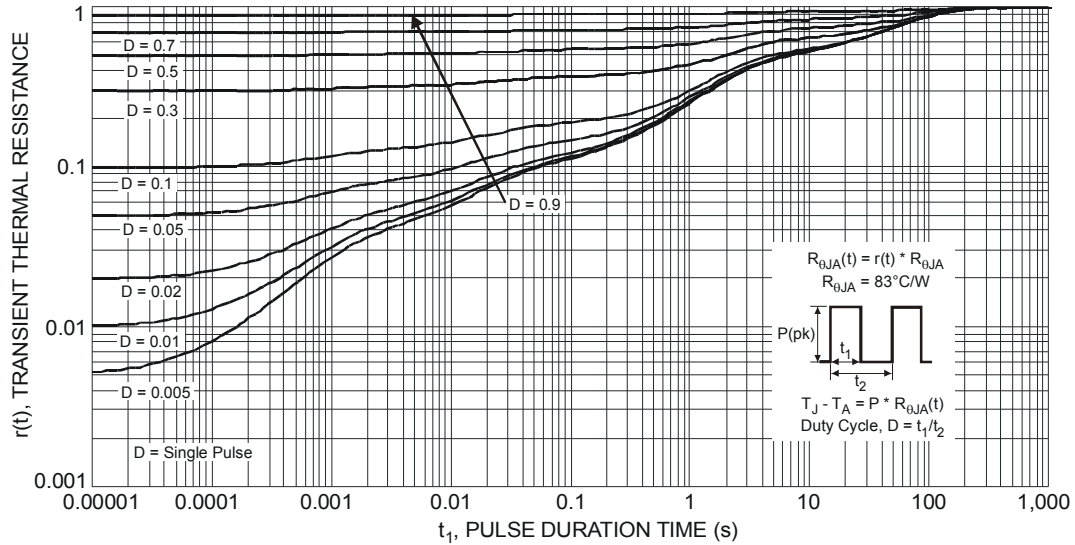
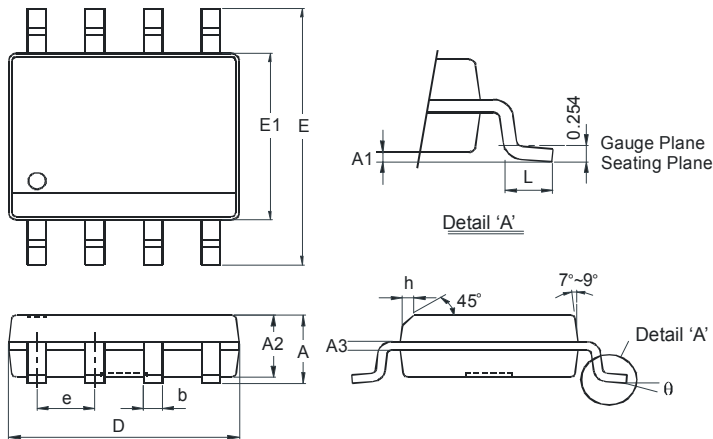


Fig. 11 SOA, Safe Operation Area



Package Outline Dimensions

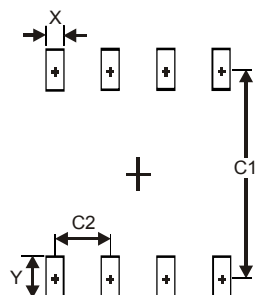
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	—	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	—	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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